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QUERY CONTROL FORM			RTIS USE ONLY	
Application No. 09/916,023	Prepared by	LM	Tracking Number	05878493
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JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION

a. Page Missing
b. Text Continuity
c. Holes through Data
d. Other Missing Text
e. Illegible Text
f. Duplicate Text
g. Brief Description
h. Sequence Listing
i. Appendix
j. Amendments
k. Other

CLAIMS

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b. Improper Dependency
c. Duplicate Numbers
d. Incorrect Numbering
e. Index Disagrees
f. Punctuation
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wherein removing a second portion of the metal oxide layer is performed in a reaction chamber in the absence of RF activation.

14 15. The method of claim 13, wherein heating the semiconductor substrate is at a temperature between about 625 degrees Celsius to 675 degrees Celsius.

15 16. The method of claim 13, wherein the semiconductor substrate comprises silicon.

16 17. The method of claim 15, further comprising:

forming a first interfacial oxide layer under the metal oxide layer;

removing at least a portion of the first interfacial oxide after removing the portion of the metal oxide layer.

12 Cont. off 4/18/04

17 18. (Amended) The method of claim 16, wherein removing at least a portion of the first interfacial oxide layer is performed using a species containing hydrogen and fluorine.

18 19. The method of claim 17, further comprising forming a second interfacial oxide over the semiconductor substrate.

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19 21. (Amended) A method of forming a metal oxide comprising:

providing a semiconductor substrate;

forming a metal oxide layer over the semiconductor substrate; and

removing a portion of the metal oxide layer by heating the semiconductor substrate and flowing a gaseous halide;

wherein removing a portion of the metal oxide layer is performed in a reaction chamber in the absence of RF activation.

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20 22. The method of claim 19, wherein the gaseous halide comprises hydrogen.

21 23. The method of claim 20, wherein the gaseous halide is HCl.

22 24. The method of claim 20, wherein the gaseous halide is HF.

23 25. The method of claim 19, wherein the metal oxide contains hafnium and oxygen.

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